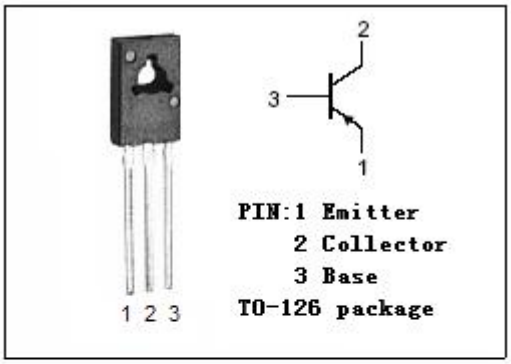
isc Silicon PNP Power Transistor — 2SA1486

DESCRIPTION

- Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$= -80V(Min)
- With TO-126 package
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

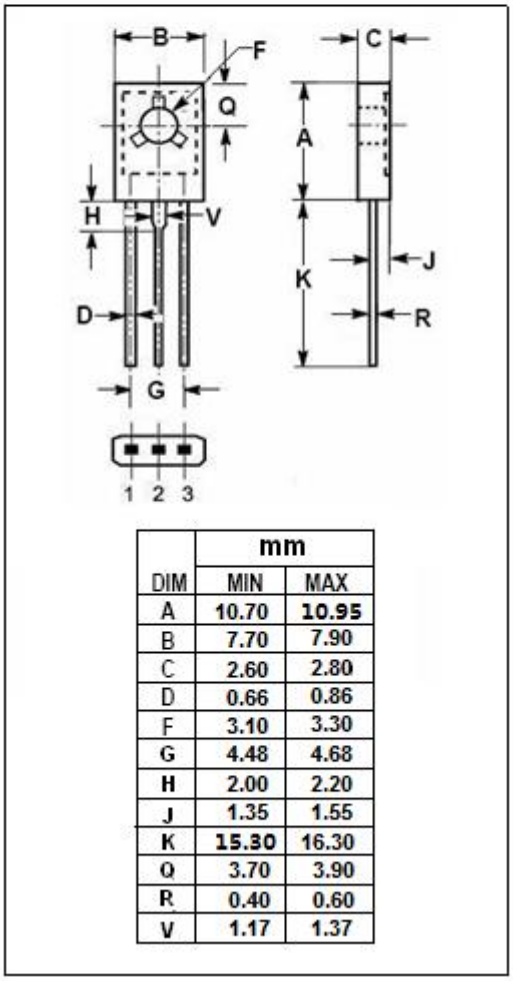


APPLICATIONS

- Designed for low frequency power amplifiers applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-600	V
V_{CEO}	Collector-Emitter Voltage	-600	V
V_{EBO}	Emitter-Base Voltage	-7	V
I_C	Collector Current-Continuous	-1	A
I_{CM}	Collector Current-Peak	-2	A
P_C	Collector Power Dissipation @Ta=25℃	1	W
	Collector Power Dissipation @T_C=25℃	10	
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55~150	℃



DIM	mm MIN	mm MAX
A	10.70	10.95
B	7.70	7.90
C	2.60	2.80
D	0.66	0.86
F	3.10	3.30
G	4.48	4.68
H	2.00	2.20
J	1.35	1.55
K	15.30	16.30
Q	3.70	3.90
R	0.40	0.60
V	1.17	1.37

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ELECTRICAL CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= -1mA; R_{BE}=∞	-600			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -0.3A; I_B= -0.06A			-1.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= -0.3A; I_B= -0.06A			-1.2	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -600V; I_E= 0			-10	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -5V; I_C= 0			-10	μA
h_{FE-1}	DC Current Gain	I_C= -0.1A; V_{CE}= -5V	30		120	
h_{FE-2}	DC Current Gain	I_C= -0.5A; V_{CE}= -5V	5			

◆ **h_{FE-1} Classifications**

M	L	K
30-60	40-80	60-120